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(54) **Title:** MULTILAYER EXTREME ULTRAVIOLET REFLECTORS

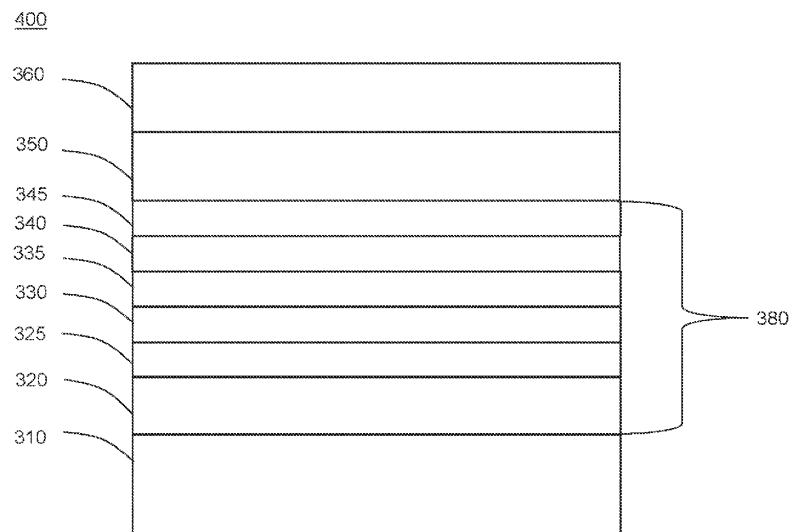


FIG. 5

(57) **Abstract:** Extreme ultraviolet (EUV) mask blanks, methods of forming EUV mask blanks and production systems therefor are disclosed. The EUV mask blanks comprise a multilayer reflective stack on a substrate. The multilayer reflective stack comprises a trilayer film including a first film, a second film, and a third film. Some EUV mask blanks include an interface layer on one or more of the first film, the second film and the third film. EUV mask blanks described herein have low Z_{eff} and high reflectance over large bandwidth of reflection angle, thereby minimizing the M3D effect, especially for high-NA EUV scanners.

[Continued on next page]

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